

Synthesis of oxygen deficient bismuth oxide photocatalyst for improved photoelectrochemical applications

Paramita Hajra; Sanjib Shyamal; Harahari Mandal; Debasis Sariket; Arjun Maity; Sukumar Kundu; Chinmoy Bhattacharya

Abstract

The present paper reports the effect of nitrogen modification on photoelectrochemical (PEC) water oxidation behavior of Bi₂O₃ semiconductor thin film. The semiconductor particles were synthesized via hydrothermal route using Bi(NO₃)₃ as a Bi³⁺ ion precursor and urea as the nitrogen source followed by drop-cast the particles and annealing the film at 600 °C. The synthesized Bi₂O₃ exhibited band gap energy of 3.01 eV, calculated from the UV-visible absorption spectrum which decreases to 2.75 eV through N-modification. Water oxidation behavior of the material has been tested through linear sweep voltammetry under periodic illumination. Highest photo-current of 180 mA cm⁻² has been measured for water oxidation reaction at 0.95 V vs. Ag/AgCl, under illumination of 35 mW cm⁻². N-incorporation can enhance the photocurrent up to 50% whereas the visible responsiveness of the material improves significantly as confirmed from electrochemical action spectra and UV-visible absorption spectra. The photocatalytic activity of the semiconductor particles was confirmed through decoloration of Rhodamine-B dye, by spectrophotometric measurements.